

INSTRUCTION DIVISION FIRST SEMESTER 2016-2017 Course Handout Part II

Date:02/08/2016

In addition to part -I (General Handout for all courses appended to the Time Table), this portion gives further specific details regarding the course.

Course No. : EEE/INSTR F 214
Course Title : Electronic Devices

Instructor-in-Charge : V K CHAUBEY (vkc@pilani.bits-pilani.ac.in)
Instructors : Abhijit R Asati, Arnab Hazra, Vinita Tiwari,kari

Babu Ravi Teja, Lucky Sharan.

1. Scope and Objective:

The course provides a comprehensive understanding of the basic theory of semiconductors and devices made out of it. Starting by explaining the fundamentals of semiconductors like energy band formation, electron and hole concepts, effect of electric and magnetic fields on charge carriers, the course helps in developing the understanding about excess carriers in semiconductors and its device application. In-depth study on 'junctions' prepares the students for even a detailed study on devices to be studied later like FET and BJT viz. commonly employed in Integrated Circuit (IC) technology. Concepts of some advanced semiconductor devices suitable for high frequency and infrared-optical range will also be discussed.

2. Text Book:

B. G. Streetman, and Sanjay Banerjee, "Solid State Electronic Devices", 6th ed., PHI learning Private Limited, New Delhi, 2009

3. Reference Books:

- 1. D A. Neaman, "Semiconductor Physics and Devices", 3rd edition, Tata Mc Graw Hill, New Delhi
- 2. M S Tyagi, "Introduction to Semiconductor Materials and Devices" John, NewYork 1991.

4. Course Plan:

Lecture	Topic	Learning Objectives	Reference
No.			to text
1-3	Introduction to subject and	Basics of Semiconductor materials,	Class notes
	review of semiconductor	Direct and Indirect semiconductors, Band gap,	and 3.1.3,
	fundamentals.	effective mass.	3.1.4, 3.2
4-5	Charge carriers in	Fermi level, equilibrium carrier concentrations,	3.3
	semiconductors,	temperature dependence, space charge neutrality	
	-		
6-7	Effect of electric and magnetic	Conductivity and mobility, Hall effect	3.4-3.5
	fields on drift of carriers		
8-10	Excess carriers in	Photon induced carrier generation, generation	4.1 - 4.4
	semiconductors	recombination of excess carriers, quasi-fermi	
		levels in non equilibrium	
11-16	PN Junction	Equilibrium conditions, Fermi levels, IV	5.2 - 5.6







BIRLA INSTITUTE OF TECHNOLOGY AND SCIENCE, Pilani

Pilani Campus

		characteristics, biasing, transient and AC conditions, secondary effects		
17-18	Metal Semiconductor Junction	Schottky Barrier, Rectifying contacts and ohmic contacts.	5.7	
19-22	Field Effect Transistors	To understand the structure and working of JFET, Metal-Semiconductor FET and MISFET, MOS capacitors (ideal and real)	6.2 – 6.4	
23-25	Field Effect Transistors	MOSFET, I-V characteristics and secondary effects	6.5 and Lecture notes	
26-30	Bipolar Junction Transistors	BJT operations, amplifications, carrier distribution, I-V characteristics etc. and secondary effects	7.3 – 7.5 and Lecture notes	
31-34	Optoelectronic devices	Photodiodes, Solar cells, LEDs, Lasers and Semiconductor Lasers	8.1 – 8.4	
35-38	High frequency and high power devices	Basic Structure and conduction mechanism of Tunnel diodes, IMPATT diodes, Gunn diodes	10.1 – 10.6	
39-40	Recent trends in semiconductor devices	Device Integration and Introduction to Integrated Circuits and recent advancement	Lecture Notes	

5. Evaluation Scheme:

Component	Duration	Marks (300)	Date & Time	Evaluation type
Mid Sem. Exam	90 mins	100	5/10 2:00 - 3:30 PM	Closed Book
Assignment		30		Quiz based on Assignments (Closed Book)
Tutorial Quizzes	10 mins	50		Closed Book
Compre. Exam.	3 hours	120	7/12 FN	Closed Book+ Open Book

- **6. Tutorials:** Tutorial sheets will be distributed in all tutorial hours.
- **7. Chamber Consultation hours**: To be announced in the class.
- **8. Notices**: All notices concerning the course will be displayed on EEE notice board.
- **9. Make-up Examination:** Make-up will be given **ONLY** in cases of <u>sickness (hospitalization)</u> or <u>urgency</u> for going out of station. (no make-up will be given for assignments and surprise quizzes)

Instructor-in-Charge EEE C381



